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N- and P-Channel 20 V (D-S) MOSFET

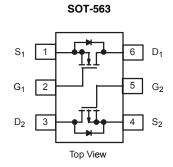
PRODUCT SUMMARY						
	V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)			
N-Channel	20	0.299 at V _{GS} = 4.5 V	1.2			
		0.426 at V _{GS} = 2.5 V	0.9			
P-Channel	- 20	0.689 at V _{GS} = - 4.5 V	- 0.5			
		0.873 at V _{GS} = - 2.5 V	- 0.4			

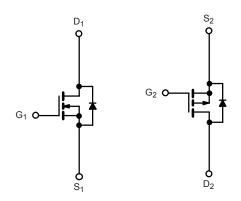
FEATURES

- DT-Trench Power MOSFET
- 100 % R_a Tested
- Compliant to RoHS Directive 2002/95/EC



COMPLIANT





N-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage		V _{DS}	20	- 20	V	
Gate-Source Voltage		V _{GS}	12	-12	V	
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 25 °C	- I _D	1.2	- 0.5		
	T _A = 70 °C		0.9	- 0.4	^	
Pulsed Drain Current		I _{DM}	3.5	- 2	Α	
w · D D · · · ah	T _A = 25 °C	P _D 1.15		5	W	
Maximum Power Dissipation ^{a, b}	T _A = 70 °C	' D	0.3		VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS Unit **Parameter** Symbol **Typical** Maximum t ≤ 10 s Maximum Junction-to-Ambient^a R_{thJA} 130 200 °C/W Maximum Junction-to-Lead Steady State $\mathsf{R}_{\mathsf{thJL}}$ 85 190

Notes

a. Surface Mounted on FR4 board.

 $b.\ t \leq 10\ s.$



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static						l .	<u> </u>	
Gate Threshold Voltage	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	N-Ch	0.4		1.2	.,	
	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 0.4		- 1.2	V	
Cata Dadi I salvasa	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V	N-Ch			± 100	nA	
Gate-Body Leakage			P-Ch			± 100		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V	N-Ch			1		
		V _{DS} = - 16 V, V _{GS} = 0 V	P-Ch			- 1		
		V _{DS} = 16V, V _{GS} = 0 V, T _J = 55 °C	N-Ch			10		
		V _{DS} = - 16V, V _{GS} = 0 V, T _J = 55 °C	P-Ch			- 5		
		V _{DS} = 5 V, V _{GS} = 10 V	N-Ch	3.5			A	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	P-Ch	- 2				
		V _{GS} = 4.5 V, I _D = 0.8 A	N-Ch		0.299	0.331	Ω	
		V _{GS} = -4.5 V, I _D = -0.4 A	P-Ch		0.689	0.760		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 0.5 A	N-Ch		0.426	0.470		
		V _{GS} = - 2.5 V, I _D = - 0.2 A	P-Ch		0.873	0.997	1	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 0.8 A	N-Ch		3.1	0.007		
		V _{DS} = - 15 V, I _D = - 0.5 A	P-Ch		2.8		S	
Diode Forward Voltage ^a	V _{SD}	I _S = 0.8 A, V _{GS} = 0 V	N-Ch		0.8	1.10	V	
		I _S = - 0.6 A, V _{GS} = 0 V	P-Ch		- 0.75	- 1.2		
Dynamic ^b						I.		
Total Cata Charge	0		N-Ch		1.6	2.2		
Total Gate Charge	Q_g	N-Channel $V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 0.5 \text{ A}$	P-Ch		2.1	2.6	nC	
Gate-Source Charge	Q _{gs}	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 0.5 A	N-Ch		0.1			
Gate-Gource Charge	Q _{gd}	P-Channel	P-Ch		0.4			
Gate-Drain Charge		$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$	N-Ch		0.2			
		I _D = - 0.3 A	P-Ch	2.5	0.5	2.0		
Gate Resistance	R_g		N-Ch P-Ch	2.5		3.9 4.5	Ω	
	-		N-Ch	<u> </u>	9	4.5	+-	
Turn-On Delay Time	$t_{d(on)}$	N-Channel	P-Ch		8		1	
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_L = 15 \Omega$	N-Ch		19			
		$I_D \cong 0.5 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$	P-Ch		5.6			
Turn-Off Delay Time	t _{d(off)}	P-Channel	N-Ch		23		1	
		$V_{DD} = -15 \text{ V}, R_L = 15 \Omega$	P-Ch		12		ns	
Fall Time	t _f	$I_D \cong$ - 0.5 A, V_{GEN} = - 10 V, R_g = 6 Ω	N-Ch		7		1	
			P-Ch		6.9		_	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 0.6 A, dI/dt = 100 A/μs	N-Ch		6.3			
Course-Brain Neverse Necovery Time		$I_F = -0.6 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$	P-Ch		11			

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

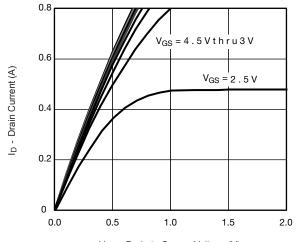
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.



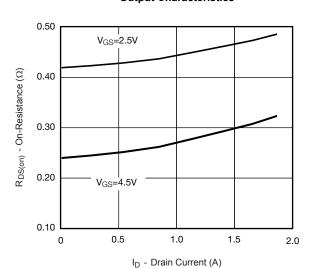
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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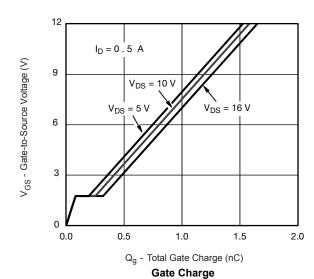


V_{DS} - Drain-to-Source Voltage (V)

Output Characteristics



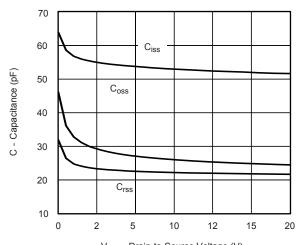
On-Resistance vs. Drain Current



1.0 0.8 I_D - Drain Current (A) 0.6 T_C = 25 °C 0.4 $T_C = 125$ °C 0.2 - 55 °C $T_C =$ 0.0 0.0 0.3 0.6 0.9 1.2 1.5

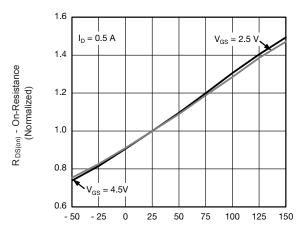
V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



V_{DS} - Drain-to-Source Voltage (V)

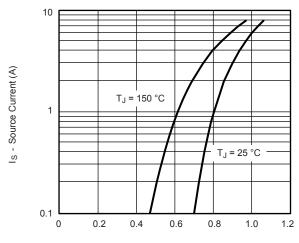
Capacitance



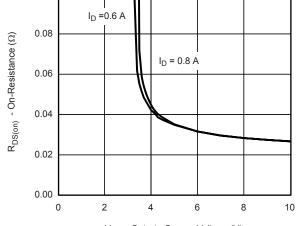
T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

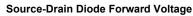


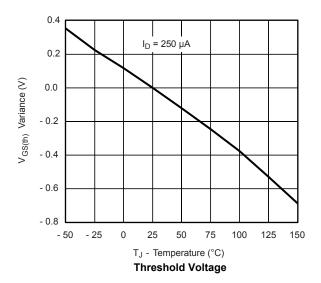
V_{SD} - Source-to-Drain Voltage (V)



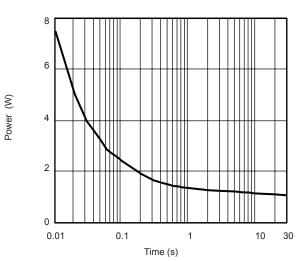
0.10

V_{GS} - Gate-to-Source Voltage (V)

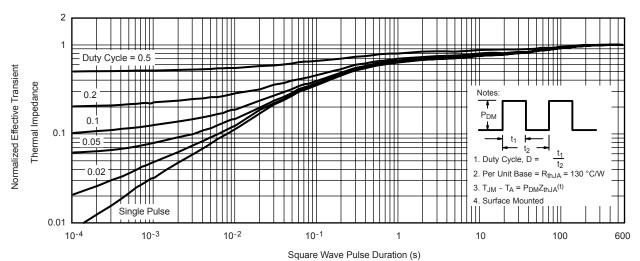




On-Resistance vs. Gate-to-Source Voltage



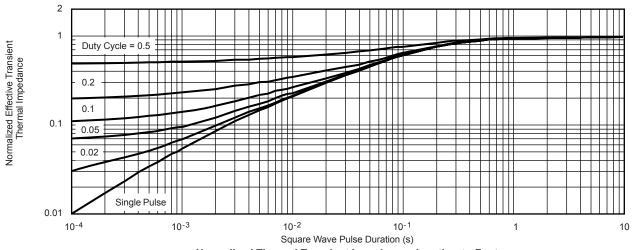
Single Pulse Power (Junction-to-Ambient)



Normalized Thermal Transient Impedance, Junction-to-Ambient

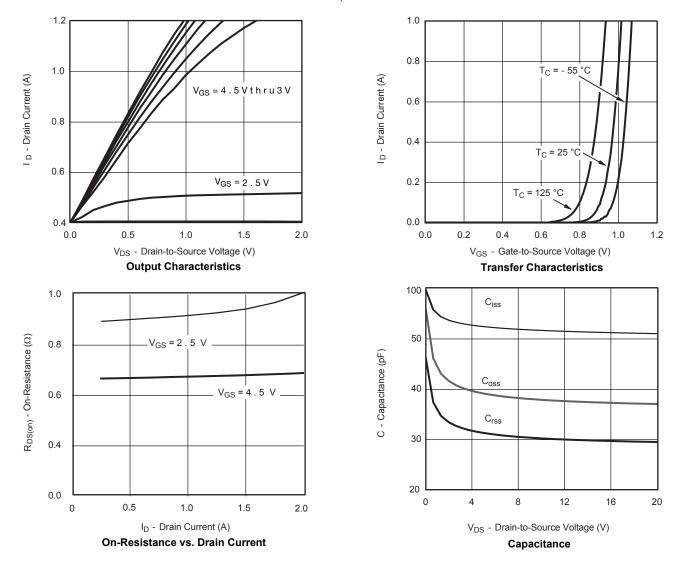


N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



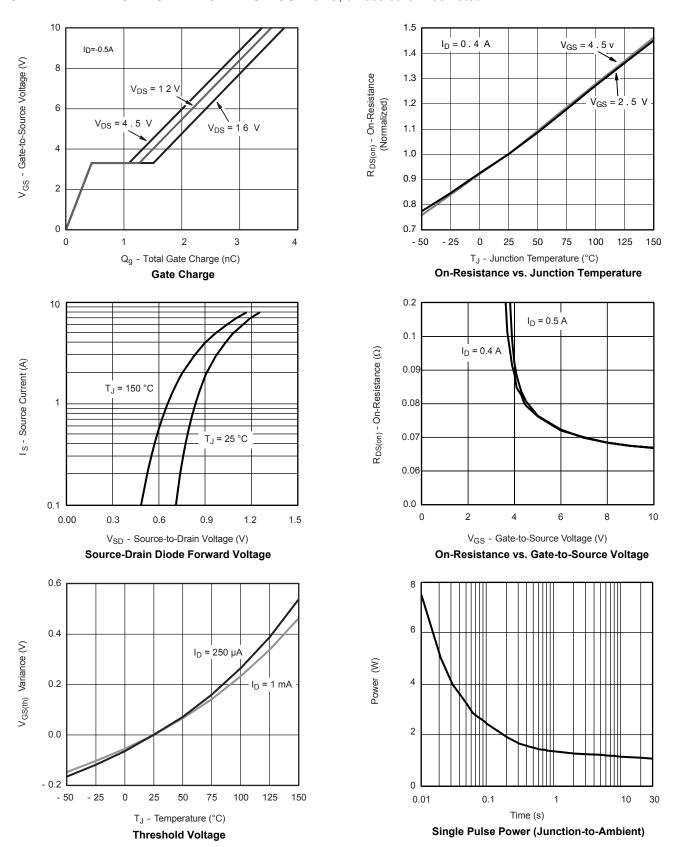
Normalized Thermal Transient Impedance, Junction-to-Foot

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



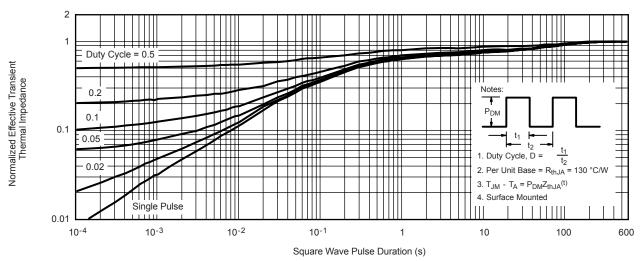


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

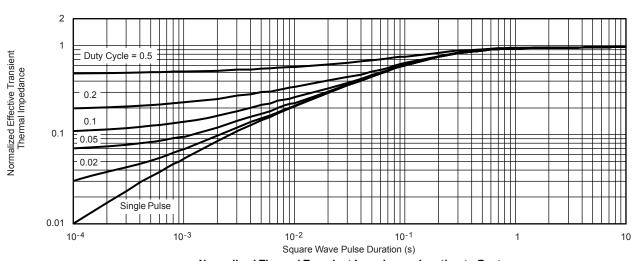




P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



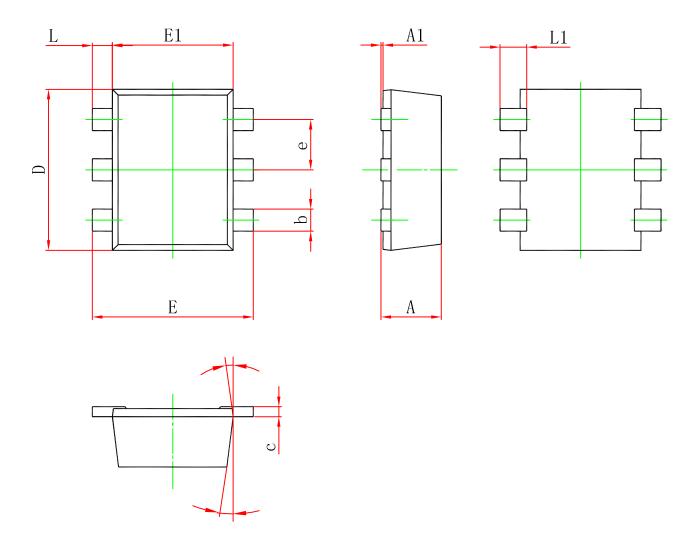
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-563 PACKAGE OUTLINE DIMENSIONS

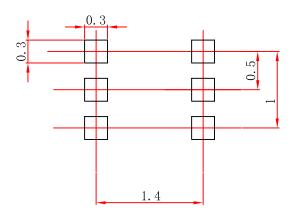


Symbol	Dimensions In Millimeters		Dimensions in inches		
Symbol	Min.	Max.	Min.	Max.	
A	0. 525	0.600	0.021	0. 024	
A1	0.000	0.050	0.000	0.002	
е	0.450	0. 550	0.018	0. 022	
С	0.090	0. 160	0.004	0.006	
D	1.500	1. 700	0.059	0. 067	
b	0.170	0. 270	0.007	0. 011	
E1	1. 100	1. 300	0.043	0.051	
Е	1.500	1. 700	0.059	0.067	
L	0.100	0.300	0.004	0.012	
L1	0. 200	0. 400	0.008	0.016	
θ	7 0	REF.	7 ⁰ I	REF.	





RECOMMENDED MINIMUM PADS FOR SOT-563



1.Unit: mm

2.Package size: 1.6*1.2

3. Tolerance: ± 0.05





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